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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

Application Number	10/728,436
Filing Date	December 5, 2003
First Named Inventor	Chen, Yung-Tin
Group Art Unit	1756
Examiner Name	Unknown

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Attorney Docket No: MA-111

**US PATENT DOCUMENTS**

Examiner Initial *	Cite No	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
<i>AB</i>	A1	6057063	05/02/2000	Liebmann et al.			
<i>AB</i>	A2	6523165	02/18/2003	Liu et al.			
<i>AB</i>	A3	6541165	04/01/2003	Pierrat			
<i>AB</i>	A4	6551750	04/22/2003	Pierrat			
<i>AB</i>	A5	6569583	05/27/2003	Cho et al.			
<i>AB</i>	A6	US20030022074A1	01/30/2003	Nolscher			

**FOREIGN PATENT DOCUMENTS**

Examiner Initials *	Cite No	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials *	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
<i>AB</i>	A7	BERNARD, DOUGLAS.A., et al., "Clear Field Dual Alternating Phase Shift Mask Lithography", <u>Optical Microlithography XV</u> , SPIE Vol. 4691, (2002),999-1008	
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	A9	CHA, HAN-SUN., et al., "A Study on Optimization of Alternating Phase Shifting Mask Structure", <u>21st Annual BACUS Symposium on Photomask Technology</u> , SPIE Vol.4562, No. II, (2002),1008-1016	
	A10	FERGUSON, RICHARD.A., "Pattern-Dependent Correction of Mask Topography Effects for Alternating Phase-Shifting Masks", <u>SPIE Vol. 2440</u> , (2/95),349-360	
	A11	GRIESINGER, UWE., et al., "Balancing of Alternating Phase Shifting Masks for Practical Application: Modeling and Experimental Verification", <u>Proc. of SPIE</u> , Vol. 4186, (2001),372-383	
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	A14	KANG, MYUNG-AH., "Feasibility evaluations of alternating phase shift mask for imaging sub-80nm feature with KrF", <u>Optical Microlithography XVI</u> , SPIE Vol. 5040, (2003),1115-1124	
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	A19	LIN, CHIH-CHENG., et al. , "Alternating PSM defect printability at 193-nm wavelength", <u>21st Annual BACUS Symposium on Photomask Technology Vol. 4562, No.II, SPIE, (2002),1121-1125</u>	
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	A21	MISAKA, AKIO., et al. , "Improved outline phase shifting mask for reduction of the mask error enhancement factor", <u>Optical Microlithography XVI, Proceedings of SPIE, Vol. 5040, (2003),1220-1230</u>	
	A22	MURAI, SHIAKI., et al. , "Establishment of Production Process and Assurance Method for Alternating Phase Shift Masks", <u>20th Annual BACUS Symposium on Photomask Technology, SPIE Vol. 4186, (2001),890-901</u>	
	A23	PETERSEN, JOHN.S. , et al. , "Designing Dual-Trench Alternating Phase-Shift Masks for 140 NM and Smaller Features Using 248 NM KRF and 193 NM ARF Lithography", <u>Proc. of SPIE, Vol. 3412, (1998),503-520</u>	
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	A25	PIERRAT, CHRISTOPHE., et al. , "New alternating phase-shifting mask conversion methodology using phase conflict resolution", <u>Optical Microlithography XV, Vol. 4691, No. I, SPIE, (2002),325-335</u>	
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		(2003), 1125-1136	
FB	A30	THIELE, JORG., et al. , "Introduction of full level alternating phase shift mask technology into IC manufacturing", <u>Optical Microlithography XV</u> , Vol. 4691, No. I, SPIE, (2002), 89-97	
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